

FERROELECTRIC MEMORY

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Abstract of JP 2001148190 (A)

PROBLEM TO BE SOLVED: To provide a ferroelectric memory, in which capacity of capacitors is increased by realizing easily high density integration preventing reduction of the number of times of repeated use of a ferroelectric memory.

SOLUTION: This memory has unit cells(UC) arranged alternately at each bit line (BL0, BL1, etc.), and connected in series respectively, dummy cells (DC0, DC1, etc.), connected to the prescribed position of each bit line and consisting of a transistor and a capacitor, transistors connecting and cutting coupling between unit cells in a bit line corresponding to each dummy cells, corresponding to a signal from the outside, and switching transistors (ST0, ST1, etc.), eliminating stored information of each dummy cell in accordance with a signal from the outside at the time of read-out of data,; a capacitor dielectric substance film has not a spontaneous polarization characteristic, when data of an arbitrary unit cell in a specific bit line is read out, a dielectric memory provides constant voltage from a dummy cell connected to a reverse bit line to a bit line as reference voltage.

